RENESAS 8TH GEN IGBT PRESENTATION

2016/DEC

RENESAS ELECTRONICS CORPORATION 2ND SOLUTION BUSINESS UNIT.



AGENDA

1. Renesas IGBT Brief Introduction

- Activity and Policy of Renesas IGBT
- Application Example (Online- UPS)
- Product portfolio by Voltage Rating and Application
- IGBT Product line-up by Application

2. NEW Product: 8th Gen. IGBT

- New Product List for Invertor circuit
- Comparison by other company



ACTIVITY AND POLICY OF RENESAS IGBT

■High efficiency performance for energy saving

Optimizing products and solution for each application

■Long product life and stable supply ✓ Miniaturization √ High Efficiency **Built-in FRD** Low Vce(sat) Wafer & Bare-Die High speed switching **Products** High Voltage √ High Reliability **Total Solution** High short circuit Withstands time (>10us) Other power devices High temperature (Si-FRD/SiC-SBD) rating (175°C) Various products (MCU, PFC-IC, Photo-coupler)

FRD; Fast recovery Diode



Online UPS (Uninterruptible Power Supply)

Our recommend products are MCU, Coupler and IGBT of focus products.

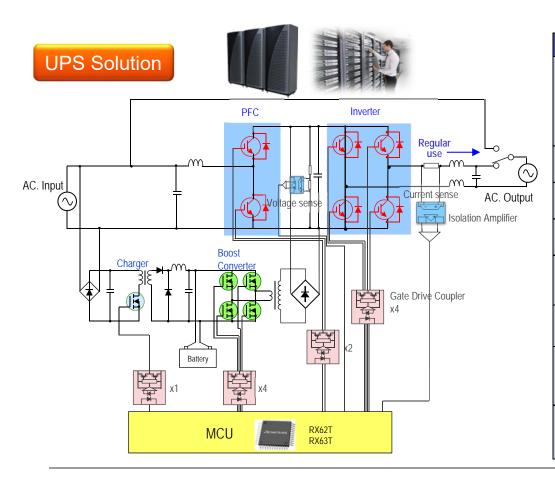
• MCU : Renesas MCU enables optimal system configuration of full digital control.

• Coupler : We will propose the coupler of required for the system.

(Gate-drive coupler, Isolation -amplifier, High Speed Optocoupler)

• IGBT : Optimize the balance of switching and conduction loss.

Realize the efficiency improvement at high output that is required with the PFC, inverter.



Recommend products	: focus products

Block	Device	Recommend products	Features			
		RX62T,63T	Ideal for continuous inverter power supply system. Three-phase PWM timer, 5V operation, A / D strengthening			
Controller	MCU	RX62G	Ideal for continuous inverter power supply system. Three-phase PWM timer, 5V operation, A / D enhanced, high-resolution PWM			
PFC (Converter)	IGBT N	<mark>EW</mark> RJH65T4xDPQ	Ideal for active filter system, high-speed switching			
Step-down converter	MOSFET	RJK50xxDPK, RJK60xxDPK	Low RDS(on), High-speed switching			
Boost converter	MOSFET	RJK1003DPN,NP70N10KUF ,Other	Low RDS(on), High-speed switching			
Inverter	IGBT	RBN40H65T1FPQ (40A @Tc=100°C) RBN50H65T1FPQ (50A @Tc=100°C) RBN75H65T1FPQ (75A @Tc=100°C)	High−speed switching,LowVCE(sat)" Low Noise Built−in FRD, Tj 175°C guarantee			
PFC Step-dow/Boost converter Inverter	Gate-drive coupler		Noise immunity (CMR≧50kV/us)(PS9031) Desat (non-saturation detection), active mirror clamp (PS9402)			
Current/Voltage sense	Photo coupler	W PS8352A	High precision (gain±1%)			
	OPamp	HA1630xxx μPC358	Small package, Low power consumption			
Photo coupler (General-Purpose)		PS23xxSeries PS27xxSeries PS28xxSeries	High isolation voltage (5kVr.m.s.), 4p-LSOP, Ta=115°C High isolation voltage(3.75kVr.m.s.), 4p-SOP, Ta=110°C High isolation voltage(2.5kVr.m.s.), 4p-SSOP, Ta=110°C			



PRODUCT PORTFOLIO BY VOLTAGE RATING AND APPLICATION

Six new product versions, rated at 650V/1250V as 8th Generation IGBTs

under development High High Robustness Wind & Solar power Invertor **High Robustness** Rating Solar Power/UPS/Industry inventor **High Speed** Voltage **High Speed Air-Conditioner** 650V **&Low Noise** / IH Cooker Solar Power/UPS/Industry inventor **Short Circuit** Strong Fast Switching Speed Robustness

IGBT Product line-up by Application

Mass ProductionUnder Develop.

	Voltage (V)	Product Series		Application									
Process				Air- conditioner (PFC/partial SW)	Air-conditioner (PFC/full SW)	Power Conditioner for PV / UPS (Inverter)			Small Fan Motor for H.A.	Renewal Energy Inventor	IH Cooker Microwave (Current Resonance)	IH Cooker Microwave (Voltage Resonance)	
			Application Required Features	Low V _{CE(sat)}	Fast Switch	Low V _{CE(sat)} Fast SW	Low V _{CE(sat)} Tsc>3us	Fast SW Tsc>5us	Fast SW Tsc>3us	Low V _{CE(sat)} Fast SW Tsc>10us	Low V _{CE(sat)} Built-in FRD	Low V _{CE(sat)} Built-in FRD	
			PKG	TO3PF	TO247	TO247	TO247 Wafer	Wafer	TO252 TO263	TO247 Wafer	TO247	TO247	
		RJH65T0x/RJH65T1x									•		
		RJH65T4x/RJP65T4x			•								
	650	RJP65T5x		0									
G7H	650	RJH65D27/RJF	P65Dxx				•						
		RJP65Mx						•					
		RJP65Sx								• (Wafer)			
	1,250	RJP1CSxx			***	42				• (Wafer)			
	650	RBNxxH65yy			Ne	0			planning	planning			
G8H	1,250	RBNxxH125yy							Ne	ew O		planning	
	1,800	RBNxxN180yy							V	0			

NEW PRODUCT: 8TH GEN. IGBT



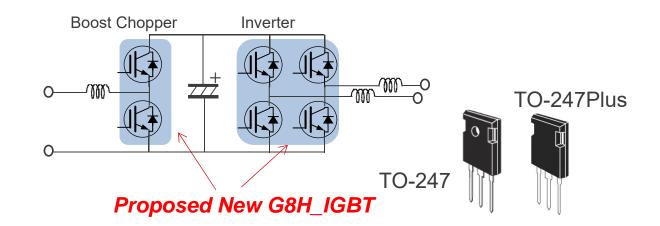
NEW PRODUCT LIST FOR INVERTOR CIRCUIT

Target Application:
 Invertor Circuit (UPS, Solar Power etc.)

Strong Point

Applied Newly developed G8H IGBT

- Low VCE(sat) and High SW Speed
- VGE ±30V Rating
- Tj 175 degC



Spec Table

P/N	VCE	VGE	IC	IF VCE(sat) [V] VF [V]		[V]	Tsc [us]	PKG		
F/IN	[V]	[V]	[A]	[A]	Тур	Max	Тур	Max	isc [us]	FNG
RBN40H65T1FPQ-A0	650V	±30	40A	30A	1.5V	2.0V	1.7V	2.2V	-	TO-247
RBN50H65T1FPQ-A0	650V	±30	50A	50A	1.5V	2.0V	2.0V	2.6V	-	TO-247
RBN75H65T1FPQ-A0	650V	±30	75A	50A	1.5V	2.0V	1.7V	2.2V	-	TO-247
RBN25H125S1FPQ-A0	1250V	±30	25A	15A	1.8V	2.34V	2.9V	3.77V	10us	TO-247
RBN40H125S1FPQ-A0	1250V	±30	40A	25A	1.8V	2.34V	2.8V	3.64V	10us	TO-247
RBN75H125S1FP4-A0	1250V	±30	75A	50A	1.8V	2.34V	2.4V	3.2V	10us	TO-247Plus

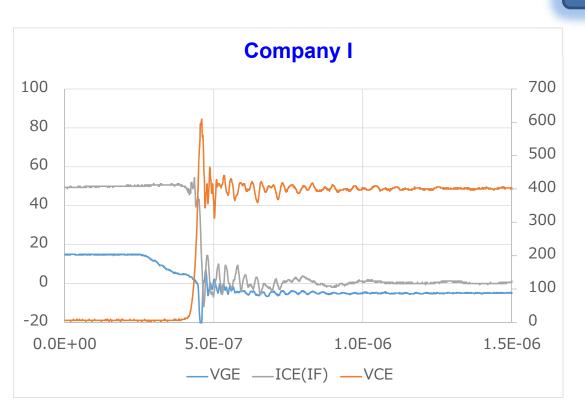
COMPARISON WITH OTHER COMPANY(650V/50A)

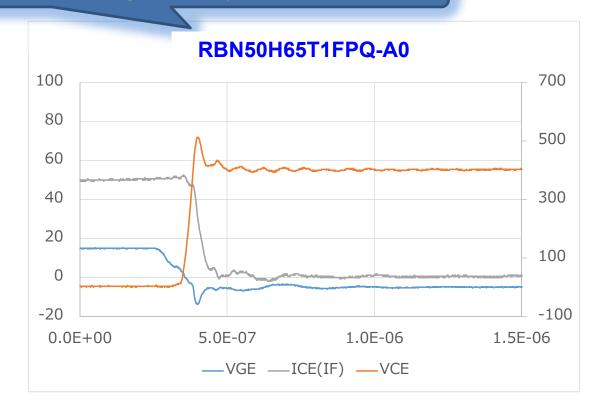
Test condition

Double pulse Switching test Ta=150°C Vin=400VDC, VG=-5V/15V Rg:on=16Ω

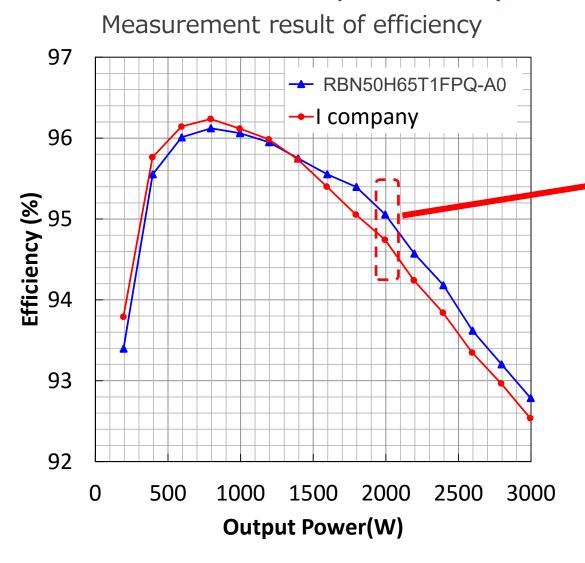
- Turn OFF Waveform

Low Switching Noise by Same condition

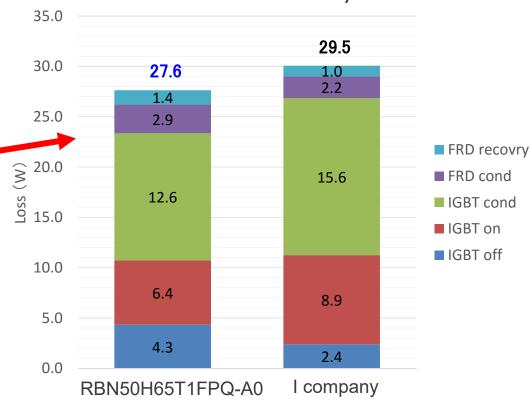




TEST RESULT (650V/50A)



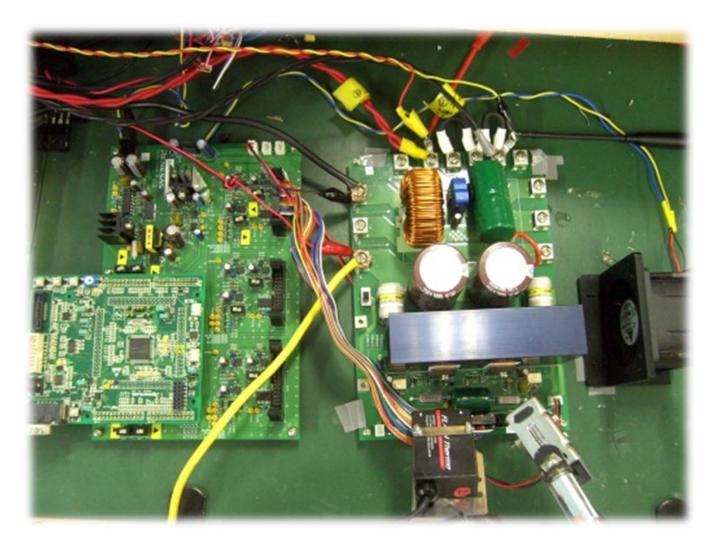




Low Noise Switching and low Loss
Achieving Higher Efficiency



INVERTOR EVALUATION BOARD



Test condition

Ta=25 degC

Vin=410VDC

Vout=100VAC(50Hz)

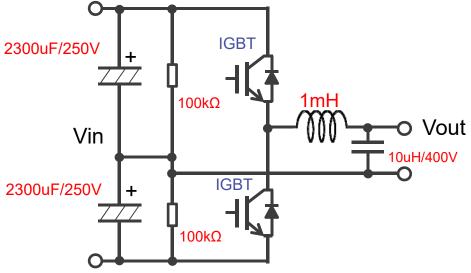
VG=-5V/15V

Rg:on=15 Ω /off=15 Ω

fsw=20KHz

Driver:PS9531

Circuit of power line





www.renesas.com

